



## CMOS Image Sensor Enhancements for Low-Light Imaging

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**ABSTRACT:** Low-light imaging poses significant challenges across domains like surveillance, mobile photography, and scientific instrumentation. CMOS image sensors have seen major enhancements to address low-light performance, particularly through innovations up to 2017. Key advancements include **backside illumination (BSI)** and **stacked CMOS** architectures that improve quantum efficiency and light capture; **pixel binning**, which aggregates signals across adjacent pixels to increase sensitivity; **advanced readout** techniques such as digital correlated double sampling (CDS) and charge-domain CDS to suppress noise; **high dynamic range (HDR)** pixel designs like LOFIC for preserving detail in dim scenes; **low-noise pixel circuits** featuring in-pixel amplification and bootstrapping for reduced read noise; and novel pixel constructs such as Geiger-mode avalanche photodiodes (GM-APDs) for photon-level detection. This paper synthesizes these pre-2018 innovations, comparing their impact on signal-to-noise ratio, sensitivity, and dynamic range. We analyze trade-offs including complexity, area, and power, and propose an integrated roadmap for next-generation low-light CMOS sensors. The study provides practical design guidance for applications requiring both high sensitivity and performance in minimal illumination.

**KEYWORDS:** CMOS image sensor; low-light imaging; backside illumination; stacked CMOS; pixel binning; CDS; low-noise pixel design; HDR; LOFIC; GM-APD.

### I. INTRODUCTION

Low-light imaging remains a fundamental challenge in CMOS sensor design. Traditional front-side illuminated sensors suffer from poor photon collection due to metallization obstructing incident light. In response, **backside illumination (BSI)** was adopted as early as 2009 with Sony's Exmor R sensors, approximately doubling sensitivity by allowing direct photon access to the photodiode Wikipedia. Stacked CMOS architectures, where sensor and circuitry layers are separated, further increased light capture and enabled advanced processing Wikipedia.

Complementary strategies include **pixel binning**, which combines signals from adjacent pixels to boost signal strength in low-light scenarios at the cost of resolution Wikipedia. Noise reduction approaches such as **digital correlated double sampling (CDS)** using CTIA pixels substantially reduce reset and fixed-pattern noise, enabling recognition under sub-lux illumination ADS. Similarly, **charge-domain CDS** and in-pixel charge sampling techniques have achieved sub-electron read noise, pivotal for photon-starved imaging imagesensors.org.

High dynamic range (HDR) pixel designs like **LOFIC/LOFITreC** augment full-well capacity via overflow capacitors, enabling over 120 dB dynamic range while managing noise trade-offs MDPI. For ultra-sensitive detection, sensors based on **GM-APD** and TDI-derived CMOS designs outperform EMCCD solutions at extreme low-light levels opticalengineering.spiedigitallibrary.orgBeijing Institute of Technology.

Finally, advanced low-noise circuits incorporating **bootstrapped resets** and optimized readout suppression deliver temporal noise well below 1 e<sup>-</sup>rms imagesensors.org. Together, these enhancements lay a multilayered foundation for next-generation low-light CMOS sensors.

### II. LITERATURE REVIEW

Significant pre-2018 advancements include:

- **Backside illumination and stacked architectures:** Sony's Exmor R (2008) introduced mass-market BSI sensors with roughly double sensitivity; Exmor RS (2012) pioneered stacked CMOS with stacked logic layers for enhanced light throughput and processing Wikipedia+1.



- **Pixel binning:** Widely adopted, pixel binning improves low-light signal capture by combining multiple pixels, achieving greater brightness albeit at lower resolution Wikipedia.
- **Noise-reduction and CDS:** Digital CDS using capacitive transimpedance amplifier (CTIA) designs reduces noise by  $7.8\times$  in dark conditions (0.1 lux), enabling usable images in very low light ADS. Charge-domain CDS and pixel-level amplification yield ultra-low noise ( $\sim 0.5$  e-rms) in standard CMOS processes imagesensors.org.
- **HDR pixel designs (LOFIC):** LOFIC and LOFITreC architectures enhance dynamic range up to  $\sim 130$  dB by providing overflow capacitors and multi-stage sampling, balancing full-well capacity and noise MDPI.
- **Photon-level CMOS designs:** GM-APD and digital TDI CMOS sensors outperform EMCCD under extreme low-light, offering superior sensitivity and SNR in imaging comparison studies opticalengineering.spiedigitallibrary.orgBeijing Institute of Technology.

These studies reflect a broad evolution: from structural sensor innovations to sophisticated pixel and circuit-level techniques targeting low-light performance.

### III. RESEARCH METHODOLOGY

We conducted a structured review focusing on pre-2018 CMOS low-light enhancements:

#### 1. Source Collection

- Reviewed academic papers, technical reports, and technology entries published before 2018 on CMOS sensor low-light innovations (BSI, stacking, binning, CDS, HDR, GM-APD).

#### 2. Classification

- Organized technologies into structural, pixel-level, readout circuitry, and system-level enhancements.

#### 3. Metric Analysis

- Evaluated reported improvements in quantum efficiency, read noise (e-rms), dynamic range (dB), and sensitivity (lx).

#### 4. Trade-Off Assessment

- Identified design trade-offs: complexity vs. performance, resolution vs. sensitivity, area vs. circuitry sophistication.

#### 5. Synthesis and Guideline Formulation

- Proposed a layered sensor enhancement roadmap optimized for low-light use: starting with structural improvements (BSI, stacking), augmenting with pixel/readout design (binning, CDS, HDR), and supplemented by advanced detection modalities for extreme applications (GM-APD).

This methodology ensures comprehensive coverage and comparative assessment of key low-light sensor techniques up to 2017.

### IV. ADVANTAGES

- **Increased Photon Sensitivity** via BSI and stacking boosts light capture significantly.
- **Enhanced Signal-to-Noise Ratio (SNR)** through pixel binning and CDS techniques.
- **Ultra-Low Noise Performance** achieved with in-pixel amplification and charge-domain readout.
- **Wide Dynamic Range** via LOFIC/HDR pixels suitable for mixed lighting scenes.
- **Extreme Low-Light Capability** with GM-APD/TDI architectures outperforming traditional EMCCDs.

### V. DISADVANTAGES

- **Fabrication Complexity:** BSI and stacking require advanced process techniques.
- **Resolution Trade-Offs:** Pixel binning reduces spatial detail in exchange for brightness.
- **Design Overhead:** LOFIC and HDR add pixel area and circuit complexity, potentially lowering fill factor.
- **Power and Area Cost:** High-performance readout circuits may increase power consumption and die area.
- **Limited Application Scope:** GM-APD sensors suited to niche or scientific domains due to complexity and cost.

### VI. RESULTS AND DISCUSSION

Reported outcomes include:

- **BSI/staked sensors** delivering  $\sim 2\times$  sensitivity improvement compared to front-side illuminated designs Wikipedia.



- **Digital CDS with CTIA pixel** enabled visible image capture at 0.1 lux and  $7.8\times$  noise reduction ADS.
- **Charge-domain CDS** and pixel amplification techniques achieved sub-electron noise levels ( $\sim 0.5$  e-rms) [imagesensors.org](http://imagesensors.org).
- **HDR LOFIC designs** offered up to  $\sim 130$  dB dynamic range without high noise penalties MDPI.
- **GM-APD CMOS sensors** outperformed EMCCD in low-light SNR metrics [opticalengineering.spiedigitallibrary.org](http://opticalengineering.spiedigitallibrary.org) Beijing Institute of Technology.

These results confirm that combining structural, pixel, and readout innovations yields measurable gains in low-light performance, while trade-offs must guide sensor architecture choices.

## VII. CONCLUSION

Pre-2018 CMOS sensor advancements dramatically improved low-light imaging capability. Through structural enhancements like BSI/stacked architectures, noise-reducing circuitry such as CDS and pixel amplification, HDR pixels, and photon-sensitive designs, CMOS sensors now offer impressive sensitivity, dynamic range, and low-noise operation. Designers must weigh trade-offs among resolution, complexity, power, and area, but these foundational enhancements empower diverse applications—from compact mobile cameras to scientific instrumentation.

## VIII. FUTURE WORK

- **Combined Architectures:** Integrate BSI, stacking, CDS, HDR, and binning in unified designs.
- **Machine-Learning Noise Reduction:** Employ deep denoising techniques tailored for hardware-specific noise signatures.
- **Event-Based Sensing:** Explore neuromorphic, asynchronous pixel readouts optimized for low-light dynamics.
- **Quantum & 2D Materials:** Investigate next-gen sensors using quantum dots or graphene for elevated sensitivity.
- **Energy-Efficient Readout:** Enhance low-light sensor systems with autonomous or energy-harvesting readout circuits.

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